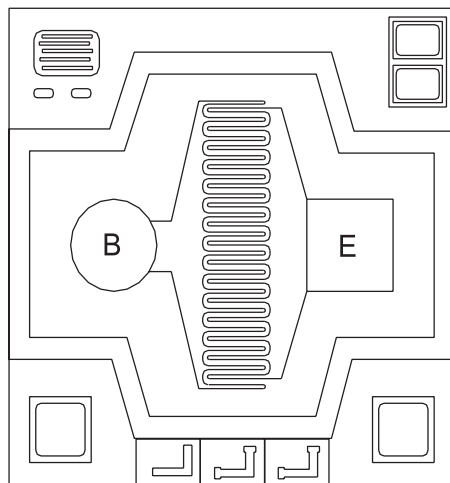


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	21.7 x 21.7 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.4 MILS DIAMETER
Emitter Bonding Pad Area	3.4 x 3.4 MILS
Top Side Metalization	Al - 10,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE COLLECTOR

R0

GROSS DIE PER 4 INCH WAFER

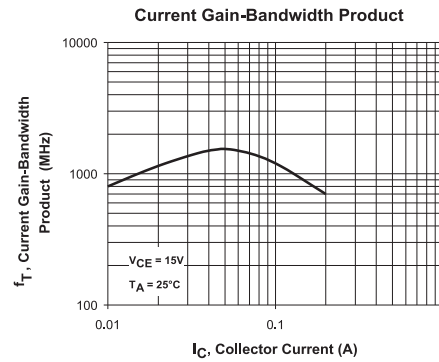
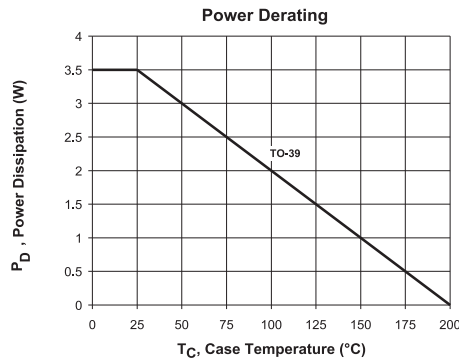
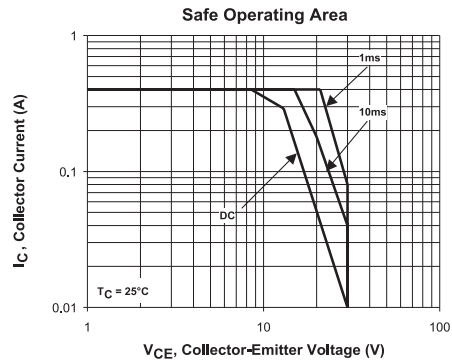
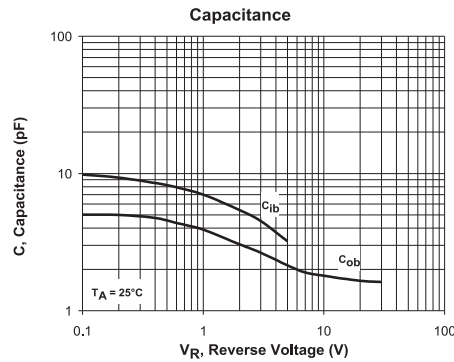
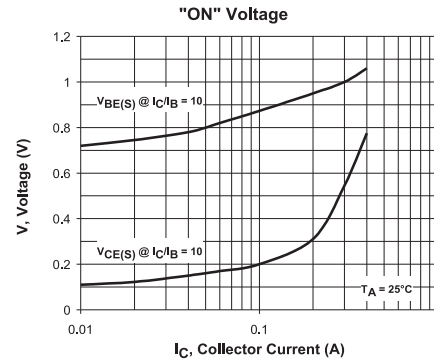
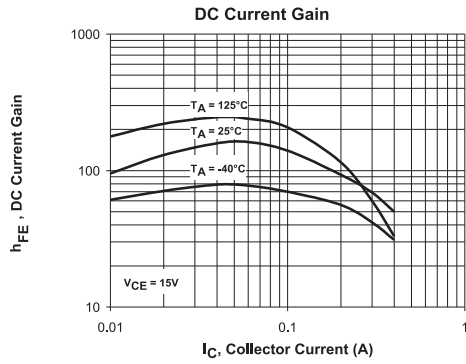
23,980

PRINCIPAL DEVICE TYPES

CM5943

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R1 (1-August 2002)



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